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THYRISTORS

BTY79 SERIES

Glass-passivated silicon thyristors in metal envelopes, intended for use in power control circuits (e.g. light and motor control) and power switching systems.

The series consists of reverse polarity types (anode to stud) identified by a suffix R: BTY79-400R to 1000R.

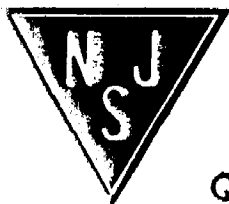
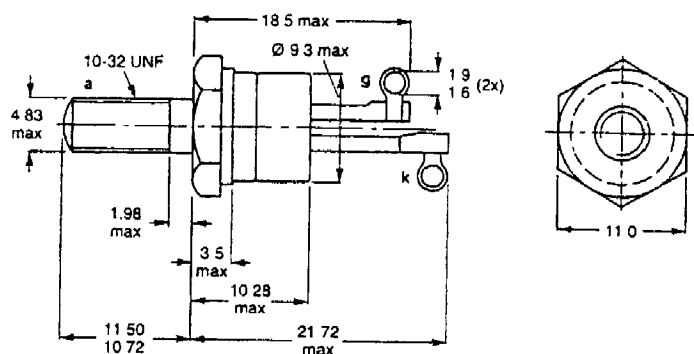
QUICK REFERENCE DATA

	BTY79-400R	500R	600R	800R	1000R
Repetitive peak voltages V_{DRM}/V_{RRM} max.	400	500	600	800	1000 V
Average on-state current			$I_{T(AV)}$ max.	10 A	
R.M.S. on-state current			$I_{T(RMS)}$ max.	16 A	
Non-repetitive peak on-state current			I_{TSM} max.	150 A	

MECHANICAL DATA

Dimensions in mm

Fig. 1 TO-64: with 10-32 UNF stud (ϕ 4,83 mm).



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

BTY79 SERIES

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Anode to cathode		BTY79-400R	500R	600R	800R	1000R
Non-repetitive peak off-state voltage ($t \leq 10$ ms)	V_{DSM}^{**} max.	500	1100	1100	1100	1100 V
Non-repetitive peak reverse voltage ($t \leq 5$ ms)	V_{RSM} max.	500	600	720	960	1100 V
Repetitive peak voltages	V_{DRM}/V_{RRM} max.	400	500	600	800	1000 V
Crest working voltages	V_{DWM}/V_{RWM} max.	400	500	600	800	1000 V*
Average on-state current (averaged over any 20 ms period) up to $T_{mb} = 85$ °C		$I_{T(AV)}$ max. 10 A				
R.M.S. on-state current		$I_T(RMS)$ max. 16 A				
Repetitive peak on-state current		I_{TRM} max. 75 A				
Non-repetitive peak on-state current; $t = 10$ ms; half sine-wave; $T_j = 125$ °C prior to surge; with reapplied V_{RWMmax}		I_{TSM} max. 150 A				
$I^2 t$ for fusing ($t = 10$ ms)		$I^2 t$ max. 112 A ² s				
Rate of rise of on-state current after triggering with $I_G = 150$ mA to $I_T = 30$ A; $dI_G/dt = 0,25$ A/ μ s		dI_T/dt max. 50 A/ μ s				
Gate to cathode						
Average power dissipation (averaged over any 20 ms period)		$P_{G(AV)}$ max. 0,5 W				
Peak power dissipation		P_{GM} max. 5 W				
Temperatures						
Storage temperature		T_{stg} -55 to +125 °C				
Junction temperature		T_j max. 125 °C				
THERMAL RESISTANCE						
From junction to mounting base		$R_{th j-mb}$ = 1,8 °C/W				
From mounting base to heatsink with heatsink compound		$R_{th mb-h}$ = 0,5 °C/W				
From junction to ambient in free air		$R_{th j-a}$ = 45 °C/W				
Transient thermal impedance ($t = 1$ ms)		$Z_{th j-mb}$ = 0,1 °C/W				

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CHARACTERISTICS

Anode to cathode

On-state voltage (measured under pulse conditions)

$$I_T = 20 \text{ A}; T_j = 25^\circ \text{C}$$

Rate of rise of off-state voltage that will not trigger any device; exponential method;

$$V_D = 2/3 V_{DRMmax}; T_j = 125^\circ \text{C}$$

Reverse current

$$V_R = V_{RWMmax}; T_j = 125^\circ \text{C}$$

Off-state current

$$V_D = V_{DWMmax}; T_j = 125^\circ \text{C}$$

Latching current; $T_j = 25^\circ \text{C}$

Holding current; $T_j = 25^\circ \text{C}$

Gate to cathode

Voltage that will trigger all devices

$$V_D = 6 \text{ V}; T_j = 25^\circ \text{C}$$

Voltage that will not trigger any device

$$V_D = V_{DRMmax}; T_j = 125^\circ \text{C}$$

Current that will trigger all devices

$$V_D = 6 \text{ V}; T_j = 25^\circ \text{C}$$

On request (see Ordering Note)

Switching characteristics

Gate-controlled turn-on time ($t_{gt} = t_d + t_r$) when

switched from $V_D = V_{DRMmax}$ to $I_T = 40 \text{ A}$;

$$I_{GT} = 100 \text{ mA}; dI_G/dt = 5 \text{ A}/\mu\text{s}; T_j = 25^\circ \text{C}$$

Circuit-commutated turn-off time when switched

from $I_T = 40 \text{ A}$ to $V_R > 50 \text{ V}$ with

$$-dI_T/dt = 10 \text{ A}/\mu\text{s}; dV_D/dt = 50 \text{ V}/\mu\text{s}; T_j = 115^\circ \text{C}$$

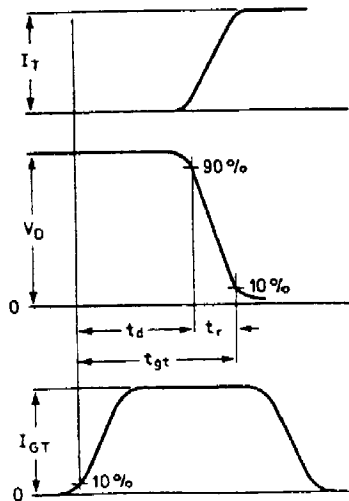


Fig. 2a Gate-controlled turn-on time definition.

V_T	<	2	V
dV_D/dt	<	200	V/ μs
I_R	<	3	mA
I_D	<	3	mA
I_L	<	150	mA
I_H	<	75	mA

V_{GT}	>	1.5	V
V_{GD}	<	200	mV
I_{GT}	>	30	mA
I_{GT}	>	20	mA

t_{gt}	typ.	2	μs
t_q	typ.	35	μs

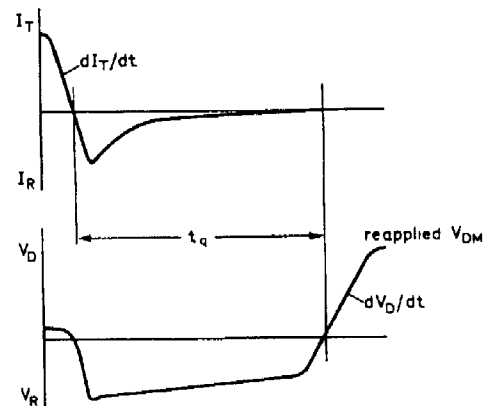


Fig. 2b Circuit-commutated turn-off time definition.